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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/864,208	05/25/2001	Norio Kimura	2001_0660A	1632
513	7590 10/04/2005		EXAM	INER
WENDEROTH, LIND & PONACK, L.L.P. 2033 K STREET N. W.			LUND, JEFFR	RIE ROBERT
SUITE 800			ART UNIT	PAPER NUMBER
WASHINGT	ON, DC 20006-1021	1763		

DATE MAILED: 10/04/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)		
	09/864,208	KIMURA ET AL.		
Office Action Summary	Examiner	Art Unit		
•	Jeffrie R. Lund	1763		
The MAILING DATE of this communication ap				
Period for Reply				
A SHORTENED STATUTORY PERIOD FOR REPL WHICHEVER IS LONGER, FROM THE MAILING E - Extensions of time may be available under the provisions of 37 CFR 1. after SIX (6) MONTHS from the mailing date of this communication. - If NO period for reply is specified above, the maximum statutory period - Failure to reply within the set or extended period for reply will, by statut Any reply received by the Office later than three months after the mailine earned patent term adjustment. See 37 CFR 1.704(b).	DATE OF THIS COMMUN .136(a). In no event, however, may a I will apply and will expire SIX (6) MO te, cause the application to become a	IICATION. a reply be timely filed DNTHS from the mailing date of this communication. ABANDONED (35 U.S.C. § 133).		
Status				
1) Responsive to communication(s) filed on <u>07</u> S	September 2005.			
2a)☐ This action is FINAL . 2b)☒ This action is non-final.				
3) Since this application is in condition for allows	•	• •		
closed in accordance with the practice under	Ex parte Quayle, 1935 C.	D. 11, 453 O.G. 213.		
Disposition of Claims				
4) Claim(s) <u>14-16, 18, 20, 23, 25, 27 and 38-40</u> is/a	are pending in the applicat	ion.		
4a) Of the above claim(s) 14 and 15 is/are wit	hdrawn from consideratio	n.		
5) Claim(s) is/are allowed.				
6) Claim(s) 16,18,20,23,25,27 and 38-40 is/are	rejected.			
7) Claim(s) is/are objected to.	as alcation societoment			
8) Claim(s) are subject to restriction and/	or election requirement.			
Application Papers				
9) The specification is objected to by the Examin	er.			
10)⊠ The drawing(s) filed on <u>08 January 2004</u> is/are		•		
Applicant may not request that any objection to the		, ,		
Replacement drawing sheet(s) including the correct				
11) The oath or declaration is objected to by the E	xaminer. Note the attach	ed Office Action or form P1O-152.		
Priority under 35 U.S.C. § 119				
12) Acknowledgment is made of a claim for foreign	n priority under 35 U.S.C.	§ 119(a)-(d) or (f).		
a)⊠ All b)□ Some * c)□ None of:				
1. Certified copies of the priority documen				
2. Certified copies of the priority documen3. Copies of the certified copies of the priority				
 Copies of the certified copies of the price application from the International Burea 		n received in this National Stage		
* See the attached detailed Office action for a list	• • • • • • • • • • • • • • • • • • • •	t received		
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uttachment(s) Notice of References Cited (PTO-892)	4) Interview	Summary (PTO-413)		
) Notice of Draftsperson's Patent Drawing Review (PTO-948)	Paper No	(s)/Mail Date		
 Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08 Paper No(s)/Mail Date) 5)	Informal Patent Application (PTO-152)		
Patent and Trademark Office	· · · · · · · · · · · · · · · · · · ·			

DETAILED ACTION

Claim Rejections - 35 USC § 103

- 1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
 - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 2. Claims 16, 23, and 38-40 are rejected under 35 U.S.C. 103(a) as being unpatentable over Laursen et al, US Patent 6,555,466, in view of Lehman et al, US Patent 6,621,264 B1, and Tsai et al, US Patent 6,117,780.

Laursen et al teaches a method of chemical mechanical planarization (polishing) of a first metal layer 2 and a second metal layer 4 that includes the steps of: polishing the first metal layer by pressing and moving the first metal layer against a polishing surface with a first polishing fluid; detecting the end point; rinsing (cleaning) the polishing surface using water; polishing the second metal layer by pressing and moving the second metal layer against the polishing surface with a second polishing fluid; and measuring the second metal layer until it reaches a second end point. (Entire document, specifically, column 3 line 65 through column 4 line 17)

Laursen et al differs from the present invention in that Laursen et al does not teach that an optical film thickness monitor measures the thickness of the second metal layer during the second polishing step, cleaning and drying the wafer, or detecting the films thickness to store or determine if the wafer is transferred to the next process.

Lehman et al teaches that an eddy current monitor works well with thick films (i.e.

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the first film) and the optical film thickness monitor works better with thin films (column 13 lines 7-43), and that the thickness measurement can be stored for future reference.

Tsai et al teaches a process that includes the steps of: polishing the wafer 220, cleaning and drying the substrate 260, measuring the films thickness 270, and determining if the wafer is transferred to the next process 280, 281. (Figure 1)

The motivation for measuring the first end point with an eddy current monitor and the second end point with an optical film thickness monitor is to use the most accurate measurement system as taught by Lehman et al in measuring the end points as required by Laursen et al but only generically described.

The motivation for motivation for cleaning and drying the wafer after processing is to remove the slurry and other polishing by-products to prevent damage to the wafer and to prepare the wafer for the next processing step as taught by Tsai et al.

The motivation for measuring the films thickness is to determine the films thickness, and to determine if the polishing step is complete.

The motivation for storing the thickness data is to have the information on the specific wafer and to create a database to help control the processing method as taught by Lehman et al.

The motivation for determining if the polishing step is done is to determine if the safer should be returned for further polishing or passed on to the next process as taught by Tsai et al.

Therefore it would have been obvious to one of ordinary skill in the art at the time the invention was made to measure the end points of Laursen et al with the eddy

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current monitor and optical film thickness monitor of Lehman et al; clean and dry the substrate, and measure the thickness of the film as taught by Tsai et al; and store the thickness data as taught by Lehman et al, or determine if the substrate should be passed to the next process as taught by Tsai et al.

3. Claims 18, 20, 25, and 27 are rejected under 35 U.S.C. 103(a) as being unpatentable over Laursen et al, Lehman et al, and Tsai et al as applied to claims 16, 23, and 38-40 above, and further in view of Hara et al, 6,451,696 B1.

Laursen et al, Lehman et al, and Tsai et al differ from the present invention in that they do not teach that the second metal layer of the substrate is pressed against the polishing surface by a load which is smaller than the load when polishing the first metal layer, the first and second polishing liquids have a PH at the same side of PH 7.

Hara et al teaches a polishing method that includes a first etching step having a load of 200 gf/cm² and a PH of 10.5, and a second etching step having a load of 100 gf/cm² and a PH of 10.5. (Column 12 lines 14-37)

The motivation for reducing the load and maintaining the PH of the slurry on the same side of PH 7 is to optimize the speed and quality of the polishing process as taught by Hara et al.

Therefore it would have been obvious to one of ordinary skill in the art at the time the invention was made to optimize the load and maintain the PH of the slurry in the method of Laursen et al, Lehman et al, and Tsai et al as taught by Hara et al.

Response to Arguments

4. Applicant's arguments with respect to claims 16, 18, 20, 23, 25, 27, and 38-40

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have been considered but are moot in view of the new ground(s) of rejection.

Conclusion

- 5. The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. The cited art teaches the technological background of the invention.
- 6. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Jeffrie R. Lund whose telephone number is (571) 272-1437. The examiner can normally be reached on Monday-Thursday (6:30 am-6:00pm).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Parviz Hassanzadeh can be reached on (571) 272-1435. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Jeffrie R. Lund Primary Examiner Art Unit 1763

JRL 10/3/05